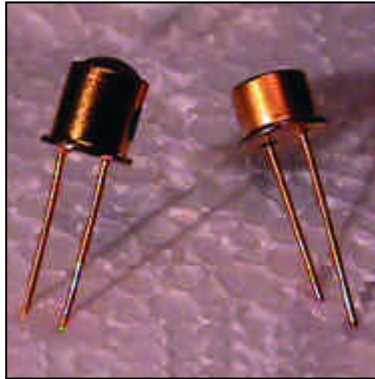
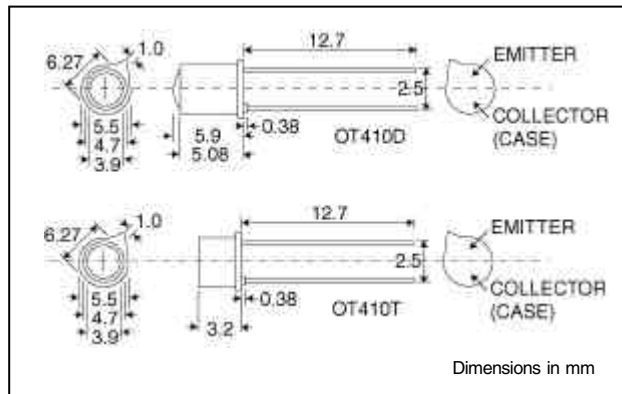


NPN Silicon Phototransistor Type OT 410D and OT 410T



The OT410 sensors consist of a high gain NPN silicon photo transistor mounted in hermetically sealed TO-46 package. These sensors are ideally suited for hostile environment operation. The OT410D features a domed lens and the OT410T a flat window.

- TO - 46 Package
- Hermetically Sealed Device ideal for hostile environments
- High Sensitivity



Specifications:

Operating Temperature Range -55°C to 125°C

PARAMETERS	SYMBOL	MIN.	TYP	MAX.	UNITS
Light Current H = 1mW/cm ²	OT 410D(T)-1 OT 410D(T)-2 OT 410D(T)-3	$I_{C(ON)}$	3 (1.5) 5 (2) 12 (4)	15 (6)	mA
Dark Current $V_{CE} = 10V, H = 0$		I_{CED}		40	nA
Collector Emitter Voltage		V_{CED}	35		V
Emitter Collector Voltage		V_{ECD}	6		V
Saturation Voltage $I_C = 1mA$		$V_{CE(SAT)}$		0.50	V
Angular Response	OT 410D OT 410T	ϕ	20 80		Deg.
Rise or Fall Time	OT 410D-1 OT 410D-6	t_r, t_f	6 8		μS
	$R_L = 100\Omega, V_{CC} = 10V$				

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